

Product Summary

| BV _{DSS} | R _{DS(ON)} Max | I _D Max T _C = +25°C |
|-------------------|-------------------------------|--|
| 60V | 50mΩ @ V _{GS} = 10V | 18A |
| | 63mΩ @ V _{GS} = 4.5V | 16A |

Features and Benefits

- Low R_{DS(ON)} – Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

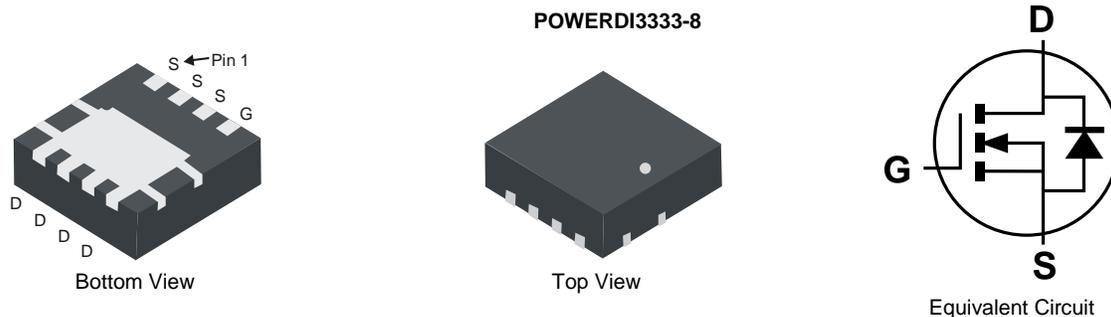
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: POWERDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓔ3
- Weight: 0.03 grams (Approximate)

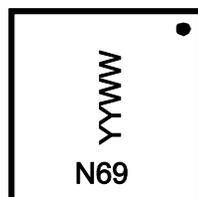


Ordering Information (Note 4)

| Part Number | Case | Packaging |
|---------------|---------------|-------------------|
| DMN6069SFG-7 | POWERDI3333-8 | 2,000/Tape & Reel |
| DMN6069SFG-13 | POWERDI3333-8 | 3,000/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



N69 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 15 = 2015)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Units |
|---|--------------|--|------------------|------------|-------|
| Drain-Source Voltage | | | V _{DSS} | 60 | V |
| Gate-Source Voltage | | | V _{GSS} | ±20 | V |
| Continuous Drain Current (Note 6) V _{GS} = 10V | Steady State | T _A = +25°C T _A = +70°C | I _D | 5.6 4.5 | A |
| | Steady State | T _C = +25°C T _C = +70°C | I _D | 18 14.5 | A |
| Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%) | | | I _{DM} | 25 | A |
| Maximum Continuous Body Diode Forward Current (Note 6) | | | I _S | 2.5 | A |
| Avalanche Current (Note 7) L = 0.1mH | | | I _{AS} | 12 | A |
| Repetitive Avalanche Energy (Note 7) L = 0.1mH | | | E _{AS} | 7.2 | mJ |

Thermal Characteristics

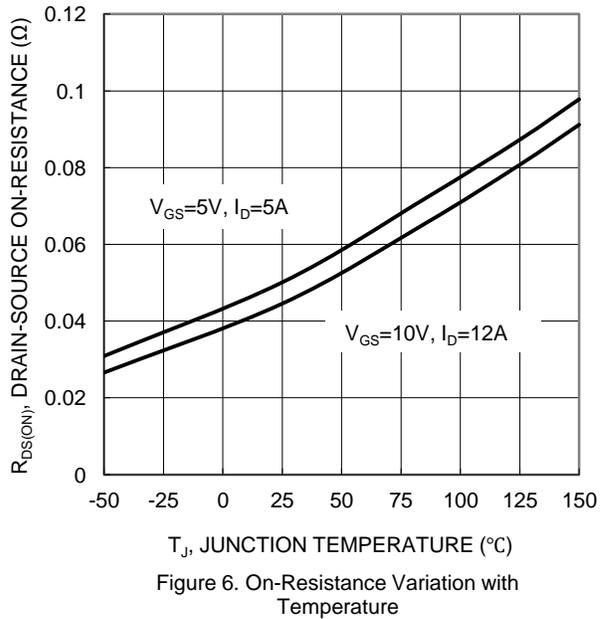
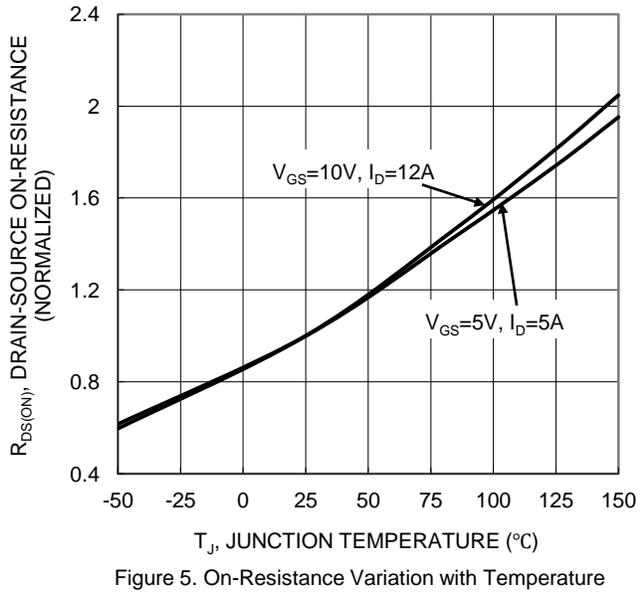
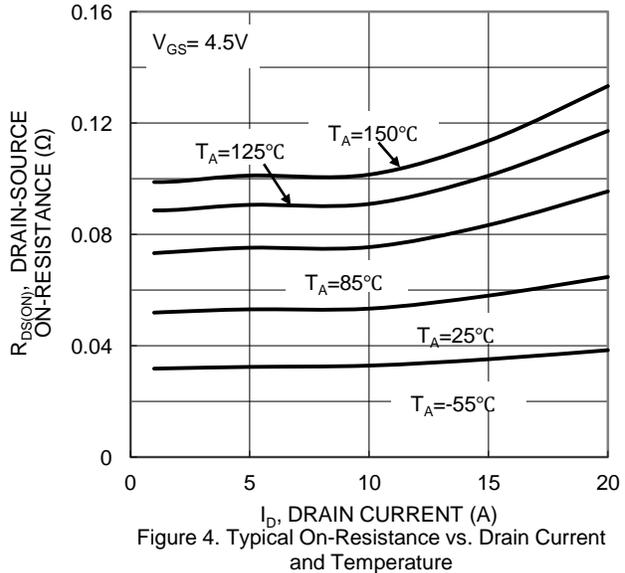
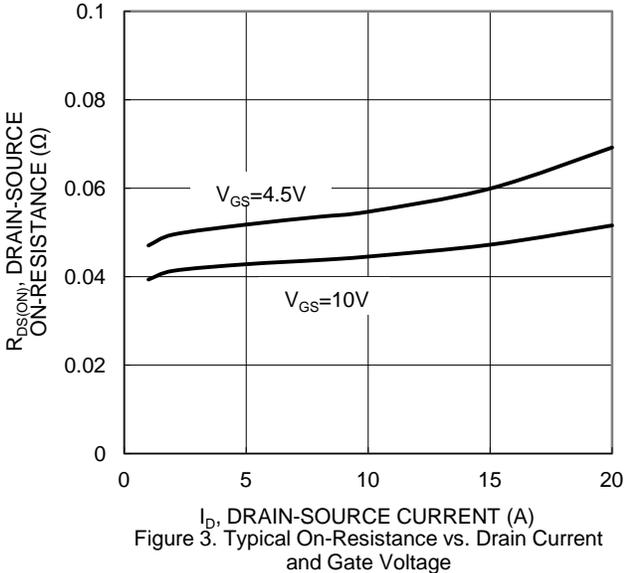
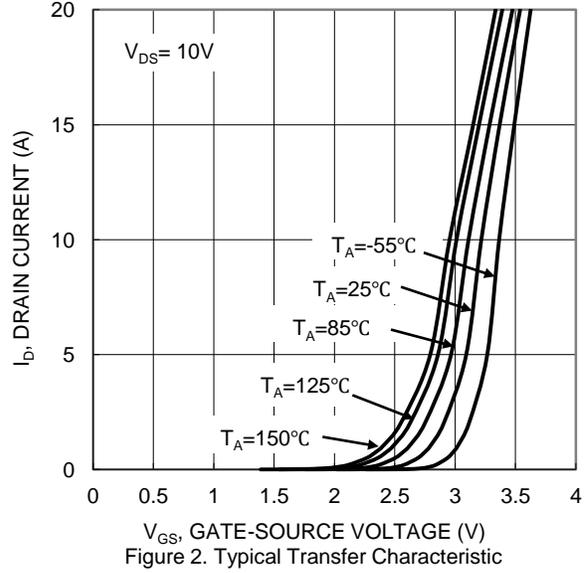
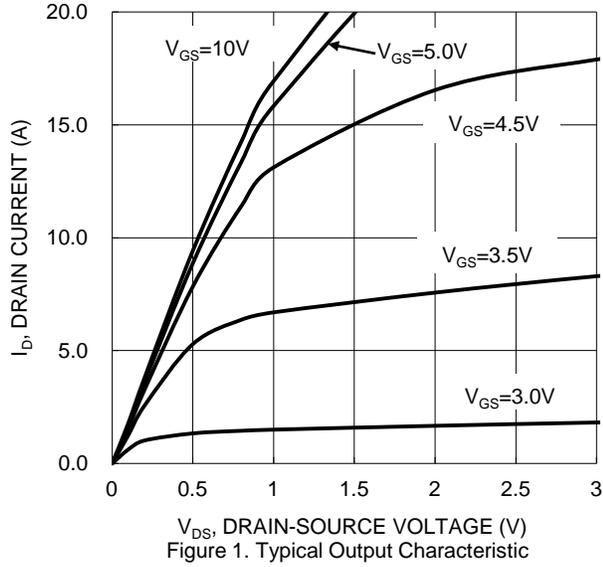
| Characteristic | | | Symbol | Value | Units |
|--|--------------|--|-----------------------------------|-------------|-------|
| Total Power Dissipation (Note 5) | | | P _D | 0.93 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | | R _{θJA} | 134 | °C/W |
| | t < 10s | | | 82 | |
| Total Power Dissipation (Note 6) | | | P _D | 2.4 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | | R _{θJA} | 53 | °C/W |
| | t < 10s | | | 33 | |
| Thermal Resistance, Junction to Case | | | R _{θJC} | 5 | |
| Operating and Storage Temperature Range | | | T _J , T _{STG} | -55 to +150 | °C |

- Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1 inch square copper plate.
 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

Electrical Characteristics ($T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|--------------|-----|-----|-----------|------------|--|
| OFF CHARACTERISTICS (Note 8) | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | 60 | — | — | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$ | I_{DSS} | — | — | 1 | μA | $V_{DS} = 60V, V_{GS} = 0V$ |
| Zero Gate Voltage Drain Current $T_J = +150^\circ\text{C}$ (Note 9) | I_{DSS} | — | — | 100 | μA | $V_{DS} = 60V, V_{GS} = 0V$ |
| Gate-Source Leakage | I_{GSS} | — | — | ± 100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ |
| ON CHARACTERISTICS (Note 8) | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | 1 | — | 3 | V | $V_{DS} = V_{GS}, I_D = 250\mu A$ |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | — | 39 | 50 | m Ω | $V_{GS} = 10V, I_D = 4.5A$ |
| | | — | 47 | 63 | | $V_{GS} = 4.5V, I_D = 3A$ |
| Diode Forward Voltage | V_{SD} | — | — | 1.1 | V | $V_{GS} = 0V, I_S = 2.5A$ |
| On State Drain Current (Note 9) | $I_{D(ON)}$ | 20 | — | — | A | $V_{DS} \geq 5V, V_{GS} = 10V$ |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | |
| Input Capacitance | C_{iss} | — | 740 | 1,480 | pF | $V_{DS} = 30V, V_{GS} = 0V,$ $f = 1.0\text{MHz}$ |
| Output Capacitance | C_{oss} | — | 40 | 80 | pF | |
| Reverse Transfer Capacitance | C_{rss} | — | 28 | 55 | pF | |
| Gate Resistance | R_g | — | 2.2 | 4 | Ω | $V_{DS} = 0V, V_{GS} = 0V, f = 1\text{MHz}$ |
| Total Gate Charge ($V_{GS} = 4.5V$) | Q_g | — | 6.4 | 12 | nC | $V_{DS} = 30V, I_D = 12A$ |
| Total Gate Charge ($V_{GS} = 10V$) | Q_g | — | 14 | 25 | nC | |
| Gate-Source Charge | Q_{gs} | — | 2.8 | 5.5 | nC | |
| Gate-Drain Charge | Q_{gd} | — | 2.3 | 5 | nC | |
| Turn-On Delay Time | $t_{D(ON)}$ | — | 3.6 | 10 | nS | $V_{DS} = 30V, I_D = 12A$ $V_{GS} = 10V, R_G = 6.0\Omega$ |
| Turn-On Rise Time | t_R | — | 5.0 | 10 | nS | |
| Turn-Off Delay Time | $t_{D(OFF)}$ | — | 12 | 24 | nS | |
| Turn-Off Fall Time | t_F | — | 3.3 | 10 | nS | |
| Body Diode Reverse Recovery Time | t_{RR} | — | 11 | 22 | nS | $I_F = 4.5A, di/dt = 100A/\mu s$ |
| Body Diode Reverse Recovery Charge | Q_{RR} | — | 5.1 | 10 | nC | |

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.



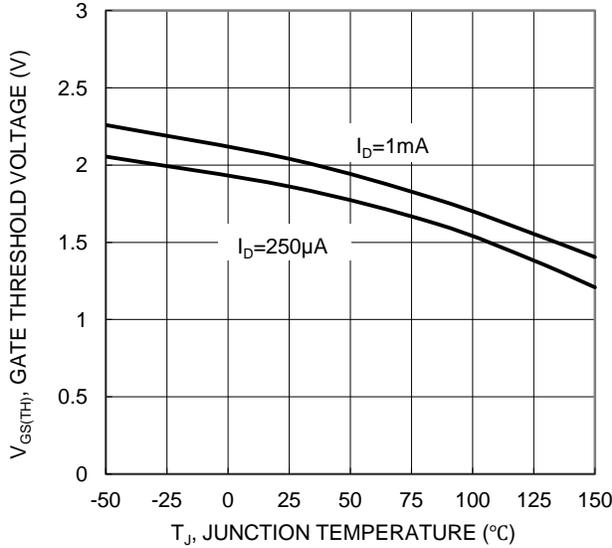


Figure 7. Gate Threshold Variation vs. Junction Temperature

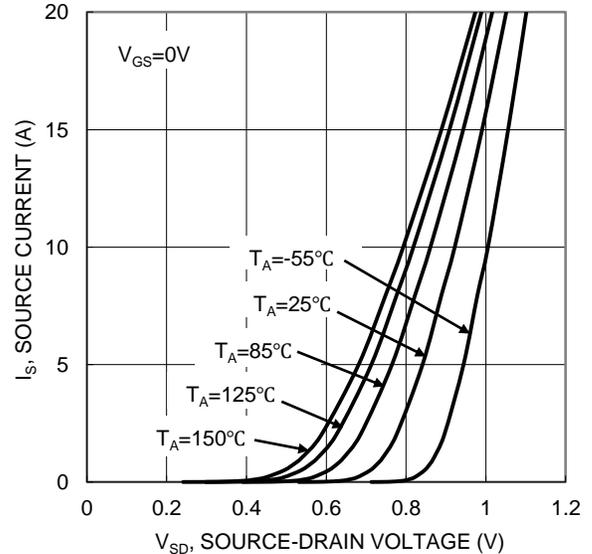


Figure 8. Diode Forward Voltage vs. Current

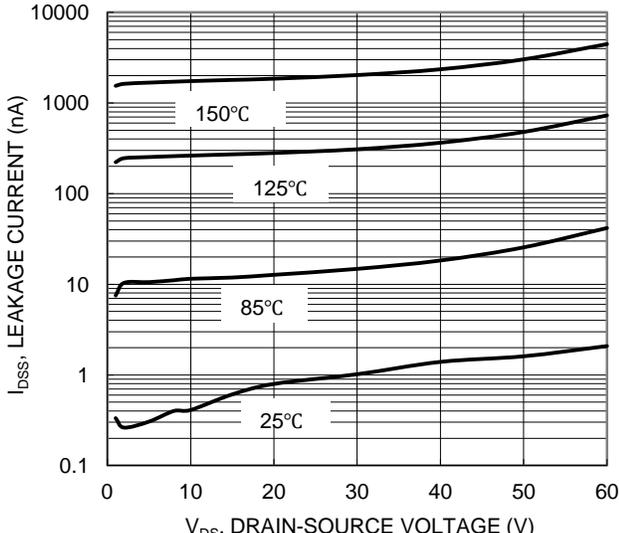


Figure 9. Typical Drain-Source Leakage Current vs. Voltage

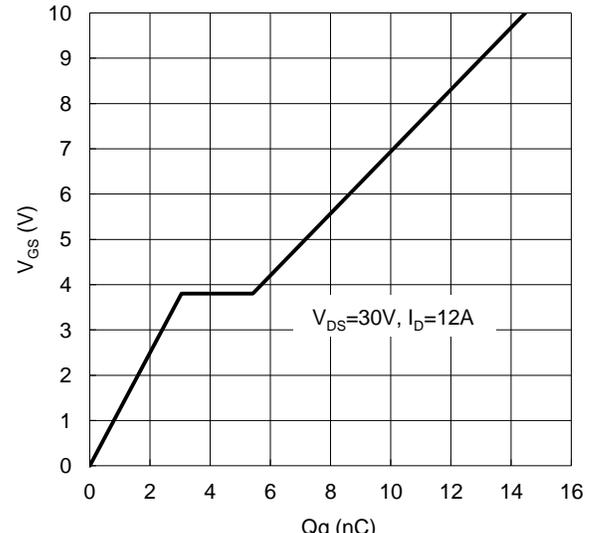


Figure 10. Gate Charge

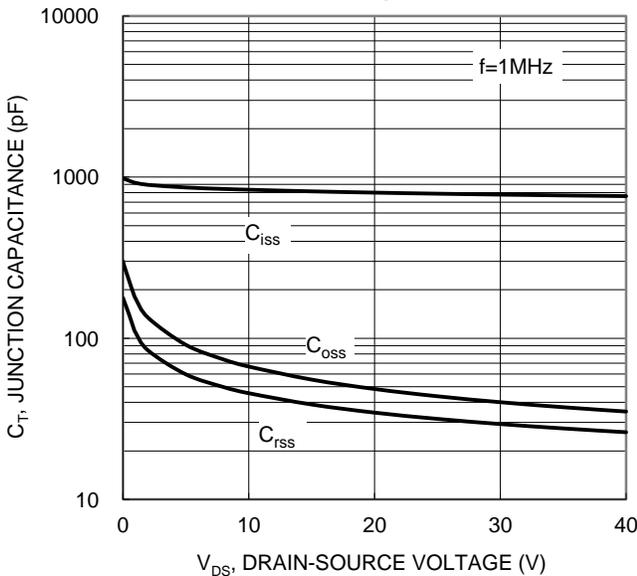


Figure 11. Typical Junction Capacitance

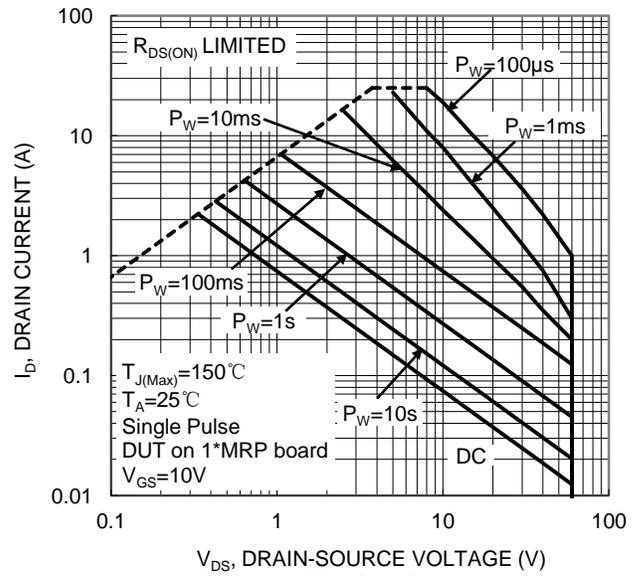


Figure 12. SOA, Safe Operation Area

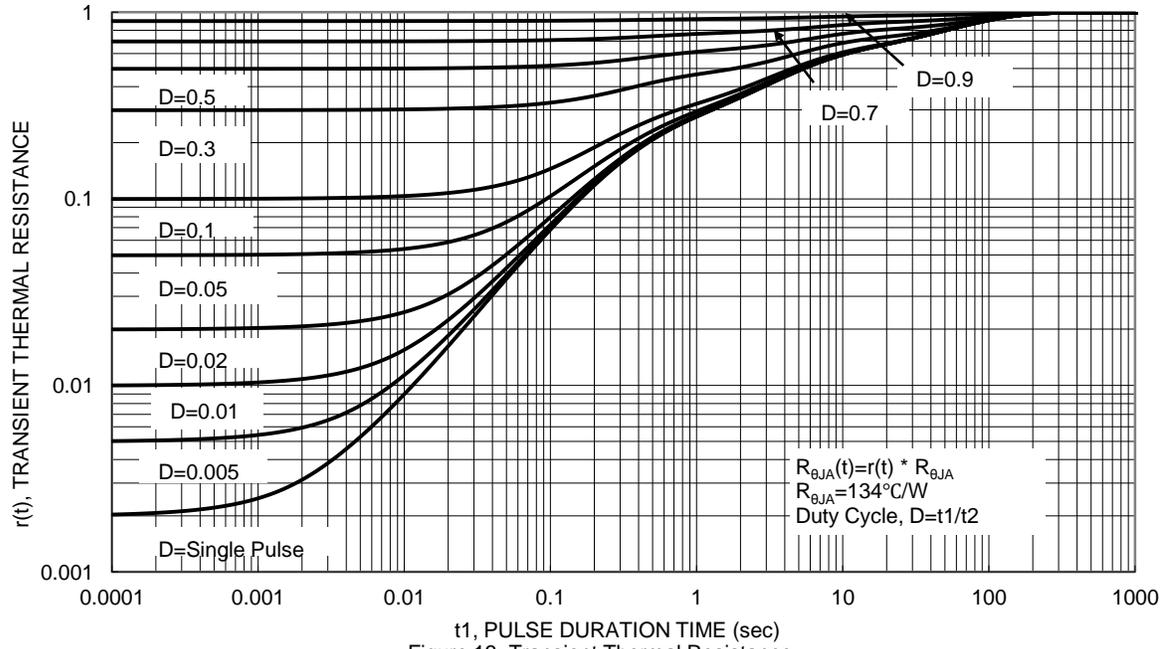
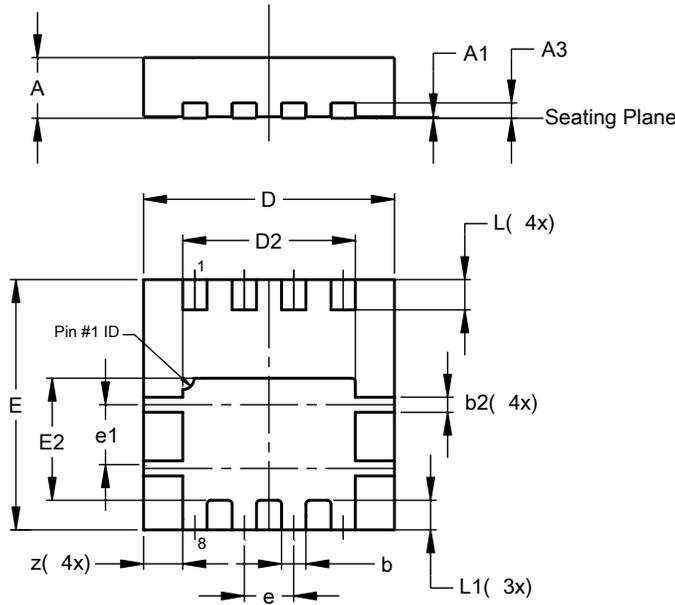


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

POWERDI3333-8

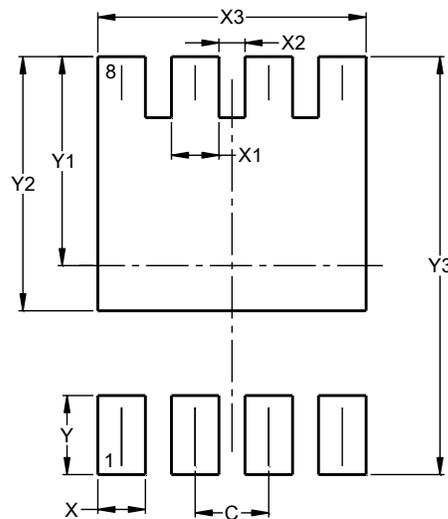


| POWERDI3333-8 | | | |
|----------------------|------|------|-------|
| Dim | Min | Max | Typ |
| A | 0.75 | 0.85 | 0.80 |
| A1 | 0.00 | 0.05 | 0.02 |
| A3 | - | - | 0.203 |
| b | 0.27 | 0.37 | 0.32 |
| b2 | - | - | 0.20 |
| D | 3.25 | 3.35 | 3.30 |
| D2 | 2.22 | 2.32 | 2.27 |
| E | 3.25 | 3.35 | 3.30 |
| E2 | 1.56 | 1.66 | 1.61 |
| e | - | - | 0.65 |
| e1 | 0.79 | 0.89 | 0.84 |
| L | 0.35 | 0.45 | 0.40 |
| L1 | - | - | 0.39 |
| z | - | - | 0.515 |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

POWERDI3333-8



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 0.650 |
| X | 0.420 |
| X1 | 0.420 |
| X2 | 0.230 |
| X3 | 2.370 |
| Y | 0.700 |
| Y1 | 1.850 |
| Y2 | 2.250 |
| Y3 | 3.700 |

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